



## Correction: Electrochemically deposited nanocrystalline InSb thin films and their electrical properties

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Correction for 'Electrochemically deposited nanocrystalline InSb thin films and their electrical properties' by K. E. Hnida et al., *J. Mater. Chem. C*, 2016, 4, 1345–1350.

There was an error in eqn (3) which was reproduced from the literature and used for the interpretation of the results. The calculations (using the equations from an original work from 1987) were done according the correct version of eqn (3) presented below:

$$\Delta E = \left[ E_g^2 + \frac{2\hbar^2 E_g \left(\frac{\pi}{r}\right)^2}{m^*} \right]^{0.5}$$

The obtained values show a decreased contribution of the quantum size effect to the  $E_g$  value. The quantum effect and Burstein–Moss effect contributions are now: 0.12 eV and 0.24 eV, respectively. Recalculated values of carrier concentration and mobility in InSb nanocrystalline films are gathered in Table 1.

Table 1 Recalculated values

	Recalculated
Effective energy band gap	0.29 eV
Quantum effect contribution	0.12 eV
Burstein–Moss effect contribution	0.24 eV
Carrier concentration $n$	$4.10 \times 10^{17} \text{ cm}^{-3}$
Carrier mobility $\mu$	$31.4 \text{ cm}^2 \text{ V}^{-1} \text{ s}^{-1}$

The change in the value of the recalculated parameters is not significant in comparison with data presented in the paper and does not affect the interpretation of the results.

The authors apologise for this oversight and for any confusion that it may have caused.

The Royal Society of Chemistry apologises for these errors and any consequent inconvenience to authors and readers.

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